

NPN General Purpose Amplifier BCP54

This device is designed for general purpose medium power amplifiers and switching circuits requiring collector currents to 1.2 A. Sourced from Process 38.

ABSOLUTE MAXIMUM RATINGS ($T_A = 25 \, ^{\circ}\text{C}$ unless otherwise noted.)

Symbol	Parameter	Ratings	Unit
V _{CEO}	Collector-Emitter Voltage	45	V
V _{CBO}	Collector-Base Voltage	45	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	1.5	Α
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. These ratings are based on a maximum junction temperature of 150 °C.
- These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

THERMAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Symbol	Characteristic	Max	Unit
P _D	Total Device Dissipation Derate Above 25°C	1.5 12	W mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	83.3	°C/W



1: Base 2, 4: Collector 3: Emitter

SOT-223 CASE 318H

MARKING DIAGRAM



A = Assembly Location

/ = Year

W = Work Week

BCP54 = Specific Device Code = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping
BCP54	SOT-223 (Pb-Free)	4,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Symbol	Parameter	Conditions	Min	Max	Unit	
OFF CHARACTERISTICS						
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10 mA, I _B = 0	45	-	V	
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	45	-	V	
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	5.0	_	V	
I _{CBO}	Collector-Cutoff Current	V _{CB} = 30 V, I _E = 0 V _{CB} = 30 V, I _E = 0, T _A = 125 °C		100 10	nA μA	
I _{EBO}	Emitter-Cutoff Current	V _{EB} = 5.0 V, I _C = 0	-	10	μΑ	
ON CHARACTERISTICS						

h _{FE}	DC Current Gain	$I_C = 5.0 \text{ mA}, V_{CE} = 2.0 \text{ V}$	25	-	
		I_C = 150 mA, V_{CE} = 2.0 V	40	250	
		I_C = 500 mA, V_{CE} = 2.0 V	25	-	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 500 mA, I _B = 50 mA	-	0.5	V
V _{BE(on)}	Base-Emitter On Voltage	$I_C = 500 \text{ mA}, V_{CE} = 2.0 \text{ V}$	-	1.0	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

BCP54

TYPICAL CHARACTERISTICS

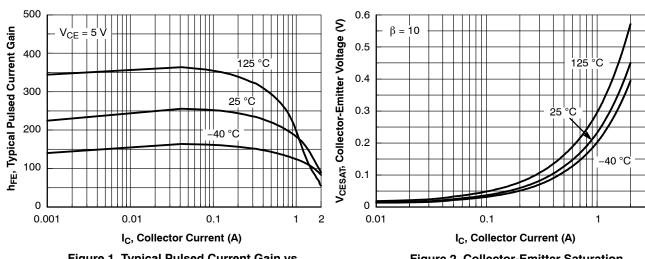


Figure 1. Typical Pulsed Current Gain vs Collector Current

Figure 2. Collector-Emitter Saturation Voltage vs Collect or Current

3

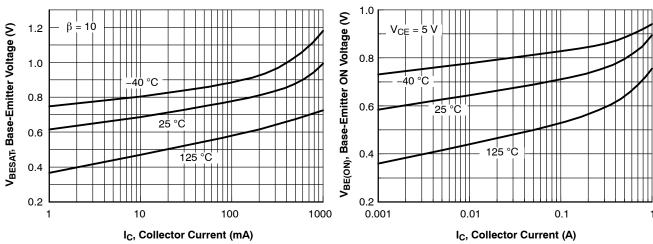


Figure 3. Base-Emitter Saturation Voltage vs Collector Current

Figure 4. Base-Emitter ON Voltage vs Collector
Current

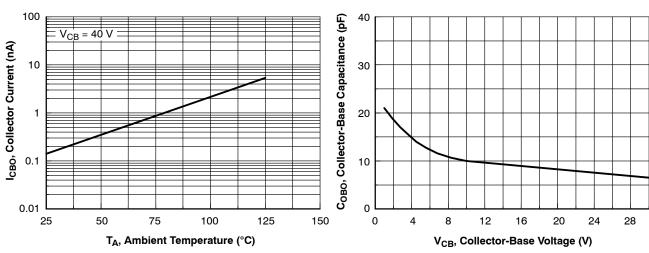


Figure 5. Collector-Cutoff Current vs Ambient Temperature

Figure 6. Collector-Base Capacitance vs Collector-Base Voltage

BCP54

TYPICAL CHARACTERISTICS (Continued)

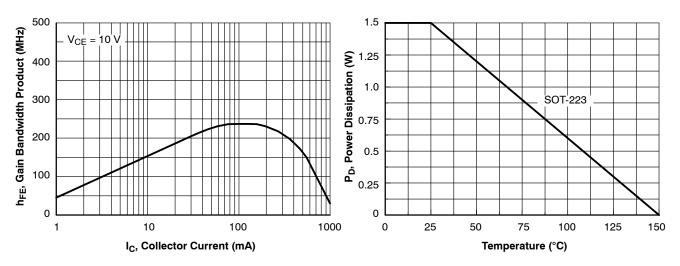
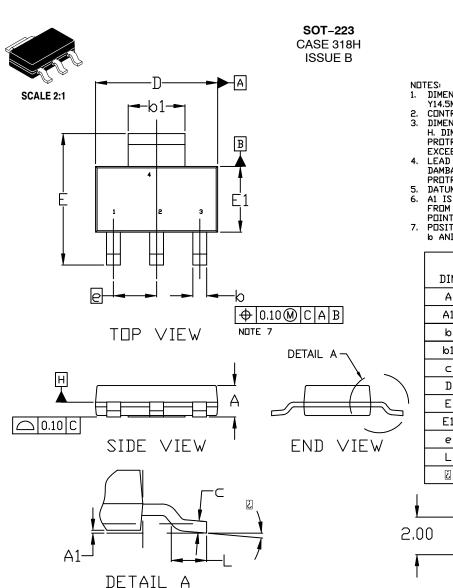


Figure 7. Gain Bandwidth Product vs Collector Current

Figure 8. Power Dissipation vs Ambient Temperature



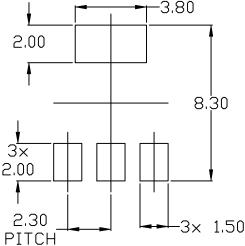


DATE 13 MAY 2020

- DIMENSIONING AND TOLERANCING PER ASME
- DIMENSIDNING AND TOLERANCING PER ASME Y14.5M, 2009.
 CONTROLLING DIMENSION: MILLIMETERS DIMENSIONS D & E1 ARE DETERMINED AT DATUM H. DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS DR GATE BURRS. SHALL NOT EXCEED 0.23mm PER SIDE.
 LEAD DIMENSIONS & AND &1 DO NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBBAR PROTRUSION. ALLOWABLE DAMBBAR PROTRUSION IS 0.08mm PER SIDE.
 DATUMS A AND B ARE DETERMINED AT DATUM H. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
 POSITIONAL TOLERANCE APPLIES TO DIMENSIONS & AND &1.

- b AND b1.

	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
Α			1.80	
A1	0.02	0.06	0.11	
b	0.60	0.74	0.88	
b1	2.90	3.00	3.10	
С	0.24		0.35	
D	6.30	6.50	6.70	
E	6.70	7.00	7.30	
E1	3,30	3.50	3.70	
е	2.30 BSC			
L	0.25			
į.	0*		10°	



GENERIC MARKING DIAGRAM*



= Assembly Location Υ

= Year

W = Work Week

XXXXX = Specific Device Code

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the IIN Semiconductor Soldering and Mounting Techniques Reference Manual, SILDERRM/D.

DOCUMENT NUMBER:	98ASH70634A	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	: SOT-223 PA		PAGE 1 OF 1	

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales